优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

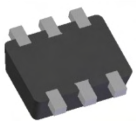
- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package

Mechanical Data

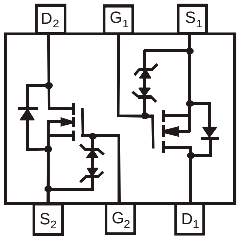
- Case: SOT-563
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish – Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.006 grams (approximate)

ESD PROTECTED TO 2kV

TOP VIEW



BOTTOM VIEW



TOP VIEW

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V_{GSS}	±6	V
Continuous Drain Current (Note 3)	Steady State	T_A = 25°C T_A = 85°C	I_D	1.38 0.89	A
Pulsed Drain Current (Note 4)			I_{DM}	3	A

Thermal Characteristics

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 3)	P_D	530	mW
Thermal Resistance, Junction to Ambient @T_A = 25°C (Note 3)	$R_{\theta JA}$	235	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Notes: 1. No purposefully added lead.

Electrical Characteristics

@T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV_{DSS}	20	-	-	V	V_{GS} = 0V, I_D = 250μA
Zero Gate Voltage Drain Current T_J = 25°C	I_{DSS}	-	-	100	nA	V_{DS} = 20V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	-	-	±1.0	μA	V_{GS} = ±4.5V, V_{DS} = 0V
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	$V_{GS(th)}$	0.5	-	1.0	V	V_{DS} = V_{GS}, I_D = 250μA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	-	0.3	0.45	Ω	V_{GS} = 4.5V, I_D = 600mA
			0.4	0.6		V_{GS} = 2.5V, I_D = 500mA
			0.5	0.75		V_{GS} = 1.8V, I_D = 350mA
			-	9		V_{GS} = 1.7V, I_D = 140mA
			-	10		V_{GS} = 1.5V, I_D = 100mA
Forward Transfer Admittance	$\|Y_{fs}\|$	-	1.4	-	S	V_{DS} = 10V, I_D = 400mA
Diode Forward Voltage	V_{SD}		0.7	1.2	V	V_{GS} = 0V, I_S = 150mA
DYNAMIC CHARACTERISTICS (Note 6)						
Input Capacitance	C_{iss}	-	60.67	-	pF	V_{DS} = 16V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	-	9.68	-	pF	
Reverse Transfer Capacitance	C_{rss}	-	5.37	-	pF	
Total Gate Charge	Q_g	-	736.6	-	pC	V_{GS} = 4.5V, V_{DS} = 10V, I_D = 250mA
Gate-Source Charge	Q_{gs}	-	93.6	-	pC	
Gate-Drain Charge	Q_{gd}	-	116.6	-	pC	
Turn-On Delay Time	$t_{D(on)}$	-	5.1	-	ns	V_{DD} = 10V, V_{GS} = 4.5V, R_L = 47Ω, R_G = 10Ω, I_D = 200mA
Turn-On Rise Time	t_r	-	7.4	-	ns	
Turn-Off Delay Time	$t_{D(off)}$	-	26.7	-	ns	
Turn-Off Fall Time	t_f	-	12.3	-	ns	

Notes: 5. Short duration pulse test used to minimize self-heating effect.
6. Guaranteed by design. Not subject to production testing.

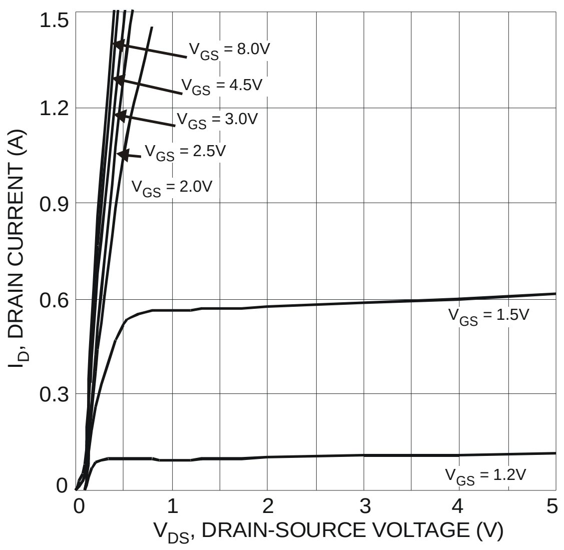


Fig. 1 Typical Output Characteristics

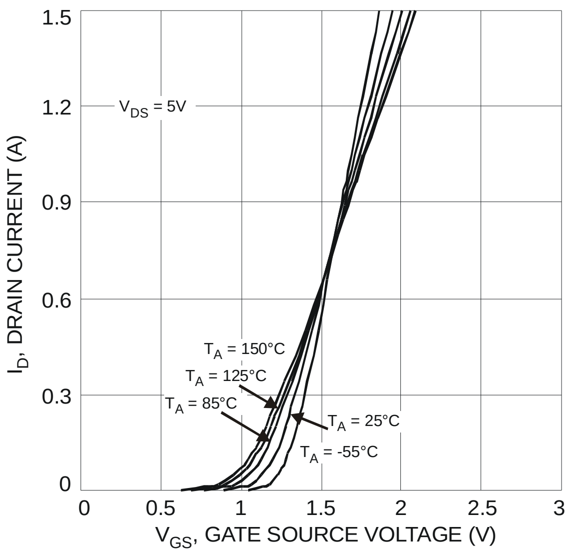


Fig. 2 Typical Transfer Characteristics

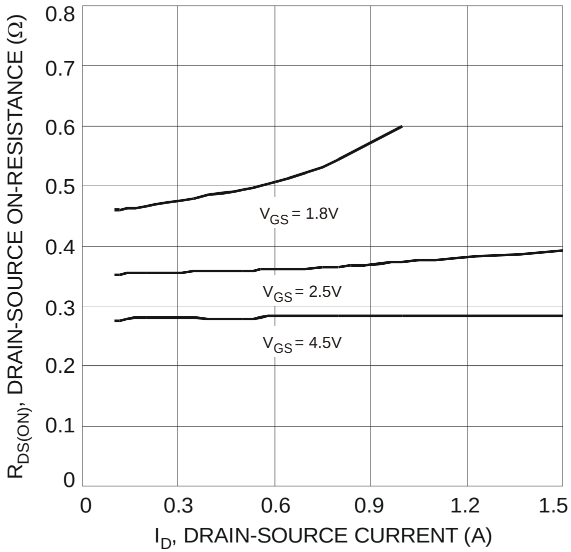


Fig. 3 Typical On-Resistance
vs. Drain Current and Gate Voltage

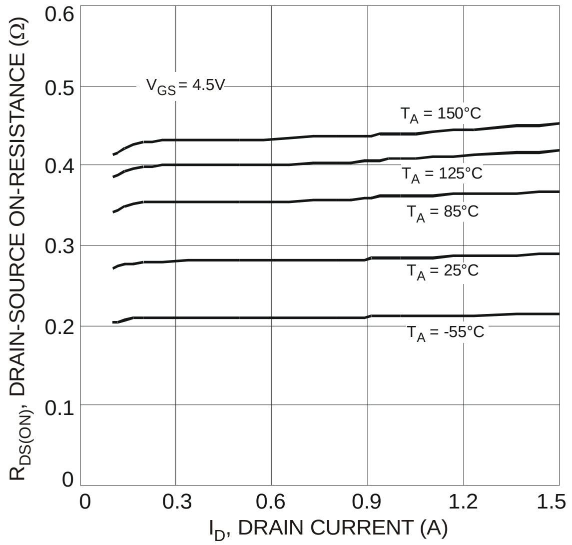


Fig. 4 Typical Drain-Source On-Resistance
vs. Drain Current and Temperature

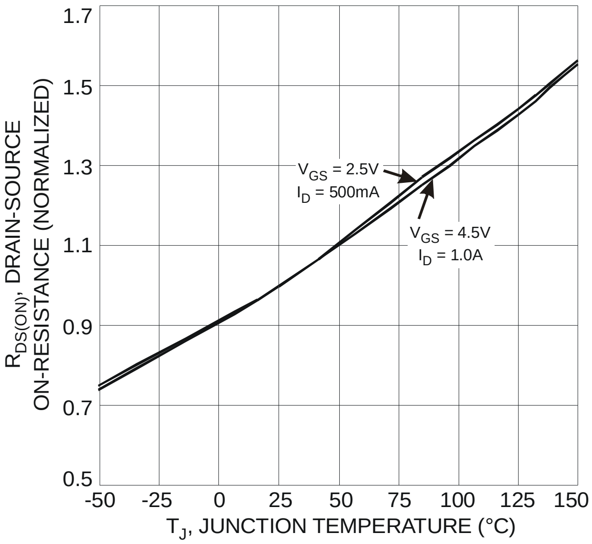


Fig. 5 On-Resistance Variation with Temperature

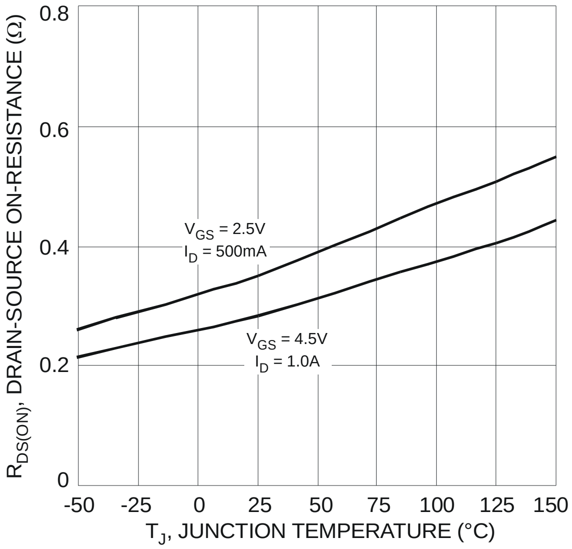


Fig. 6 On-Resistance Variation with Temperature

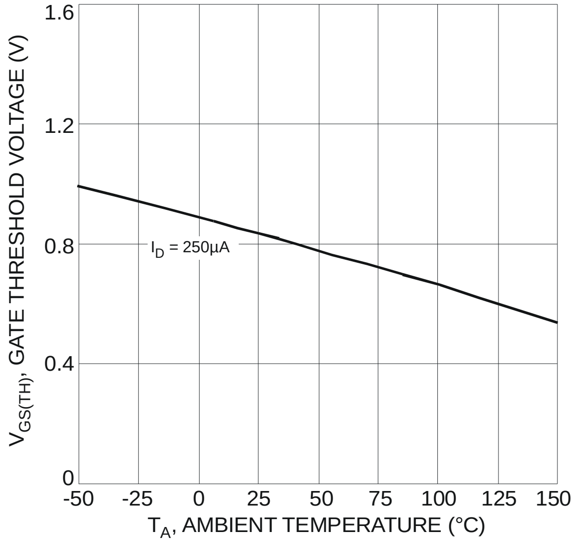


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

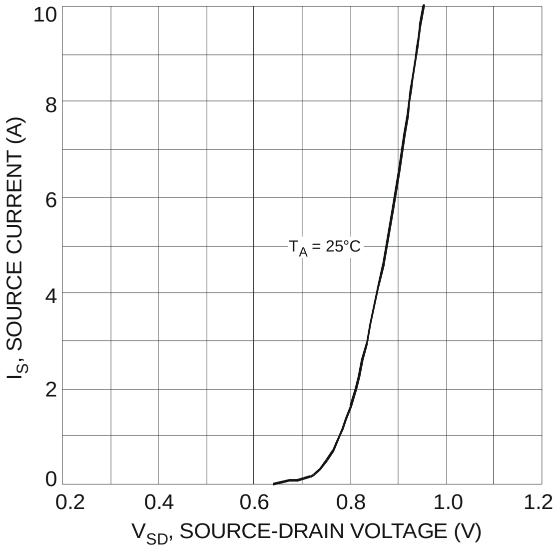


Fig. 8 Diode Forward Voltage vs. Current

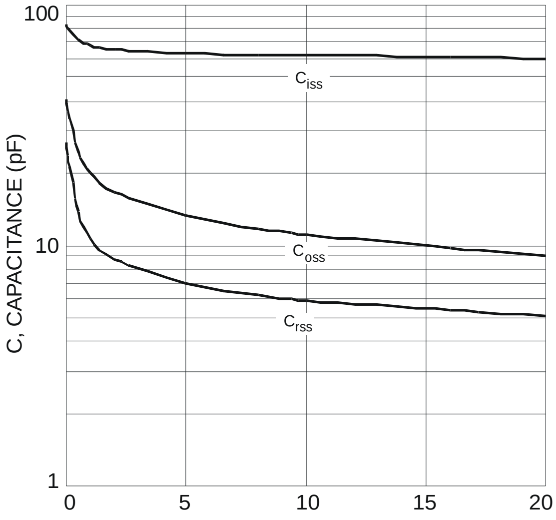


Fig. 9 Typical Capacitance

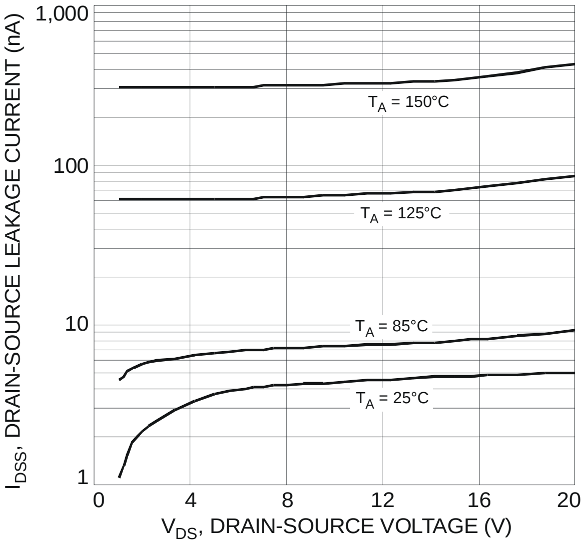


Fig. 10 Typical Drain-Source Leakage Current vs. Drain-Source Voltage

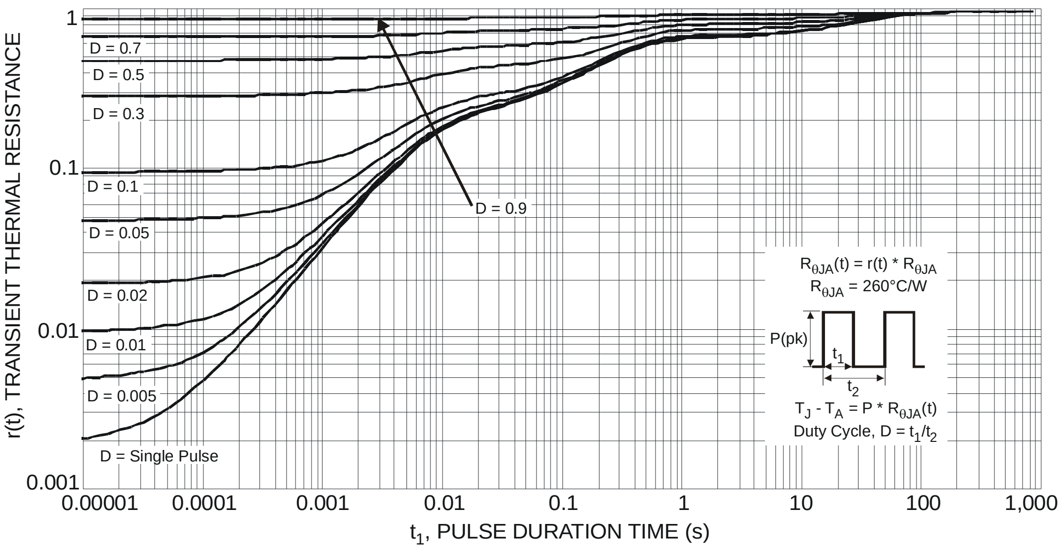
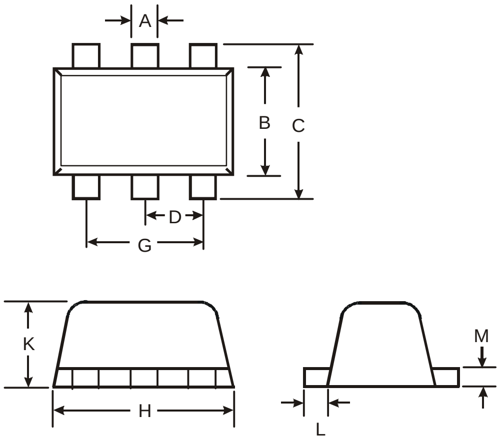


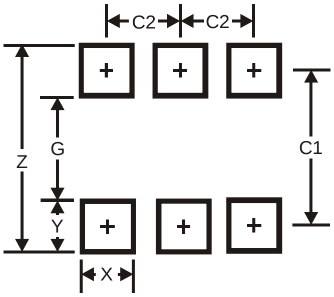
Fig. 11 Transient Thermal Response

Package Outline Dimensions



SOT-563			
Dim	**Min**	**Max**	**Typ**
A	0.15	0.30	0.20
B	1.10	1.25	1.20
C	1.55	1.70	1.60
D	-	-	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
K	0.55	0.60	0.60
L	0.10	0.30	0.20
M	0.10	0.18	0.11
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.2
G	1.2
X	0.375
Y	0.5
C1	1.7
C2	0.5